containing [the] carbon and [the] fluorine is generated fully in the plasma, and controlling a temperature of a region which forms a side wall of said vacuum processing chamber [is controlled] to have a range of 10 °C to 120 °C.

claim 7, line 3, delete "means is" and insert --produces--, same line 3, delete "source".

Claim 8, line 3, delete "means" and insert --effected using--;

line 5, after "GHz" insert --is employed--.

Claim 9, line 3, delete "means".

IN THE ABSTRACT

Please amend the abstract as follows:

Line 3, after "etching" insert --process--;

Line 4, after "ratio" insert --of--, same line 4, after
"necessary" insert --,--;

Line 5, delete "which" and insert - that the etching

characteristic fluctuates--;

Line 6, delete "an" and insert --the--, same line 6, delete "an etching characteristic is";

Line 7, delete "fluctuated", same line 7, after "Using" insert -7á--;

Line 10, delete "forming a" and insert --by maintaining the--; Line 10, delete "adjustment range", same line 10, delete "at"